Fraunhofer FEP

Fraunhofer Institute for
Organic Electronics, Electron Beam
and Plasma Technology FEP

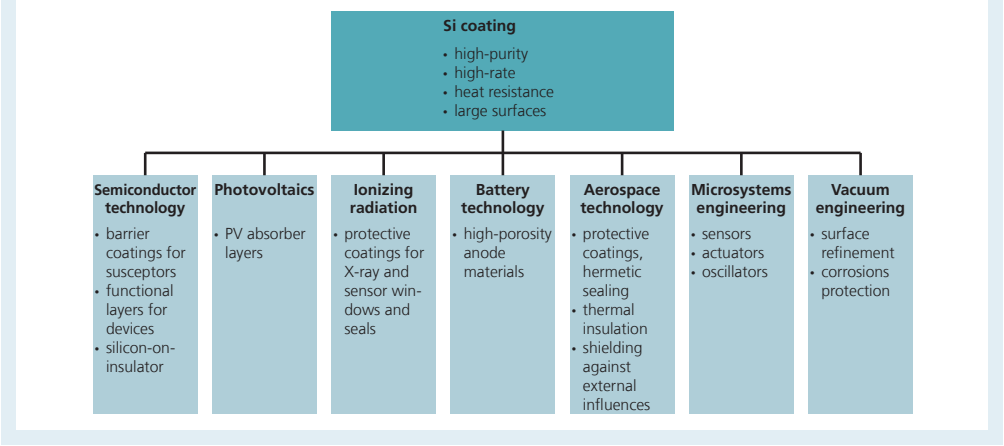
Hot polycrystalline Si brick during evaporation

High-rate deposition of pure silicon layers

Cold monocrystalline Si brick with solidified melt following evaporation

Silicon is of interest for many different applications due to its electronic properties as well as due to the diverse effects that result from its being chemically inert.

Silicon layers with suitable thickness as well as sufficient purity are necessary for many applications. A very economic way has been found to meet these requirements based on previous development work at Fraunhofer FEP. High-rate deposition of silicon layers by means of electron beam evaporation is not only attractive from an economic point of view, but also because of the high level of purity that can be achieved by this method at the same time.



Application examples

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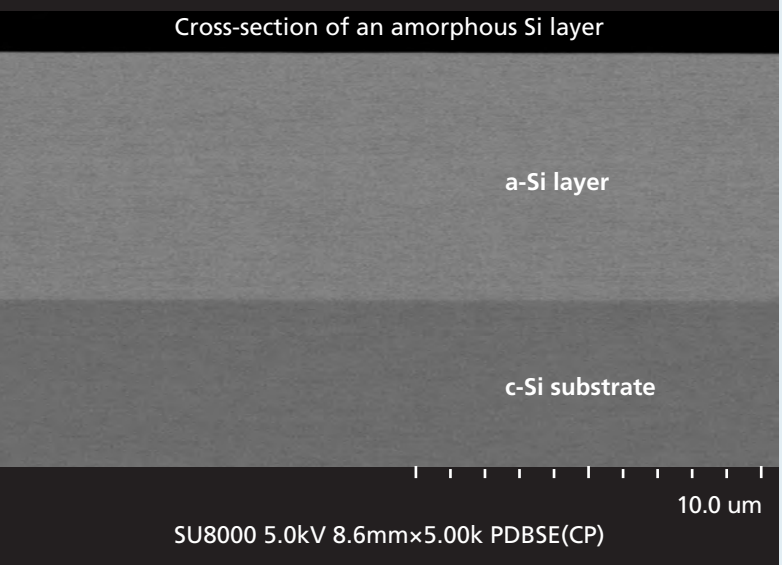

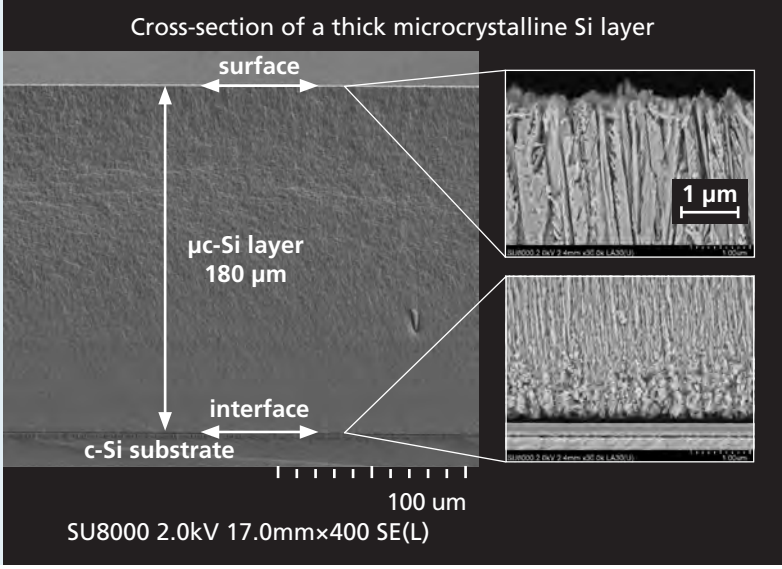

Properties

- High deposition rates (> 300 nm/s) [see Fig. 1]
- Coating of large areas (coating widths > 300 mm) [see Fig. 2]
- Layer thickness > 180 µm
- Low risk of external contaminant ingress
- High purity of layers with sufficient low metallic contamination (Fe: < 5 × 10^{14} cm^{-3}, Cu: < 3 × 10^{14} cm^{-3}) [see Fig. 3]
- Low processing temperatures feasible (< 300°C)
- Hydrogen-free layers
- Dense or porous layers (depending on requirements)
- Amorphous, microcrystalline, and polycrystalline structure (dep. on requirements)

Substrates

- Graphite components and films
- Stainless steel and other metals
- Crystalline substrates (silicon and sapphire wafers)
- Glass
- Ceramic
- Piezoelectric materials

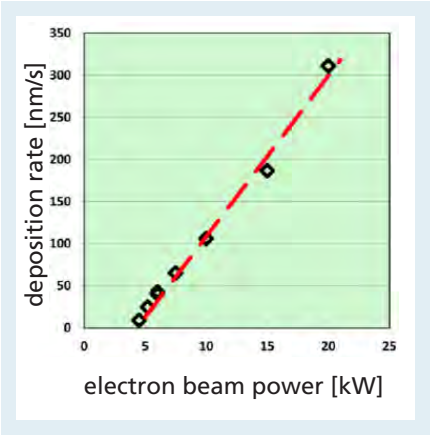

Fig. 1: Dependence of Si deposition rate on electron beam power

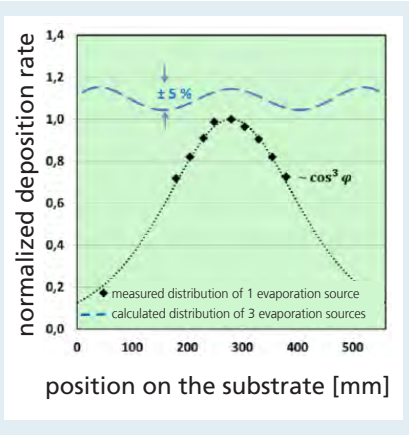

Fig. 2: Normalized lateral distribution of the Si deposition rate for single and multiple evaporation sources

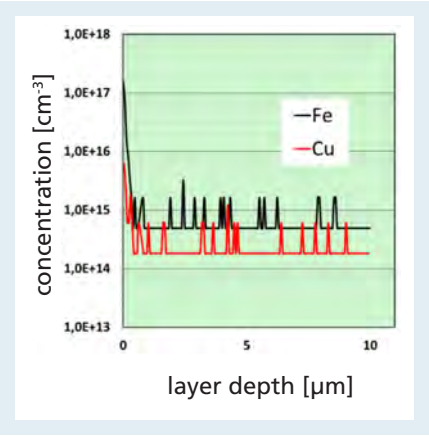

Fig. 3: Concentration depth profile of Si layer

Our offer

- Feasibility studies
- Technology development
- Determining optimal process parameters
- Integration of pre- and post-processing is available
- Pilot experiments
- Analytical capabilities for processes and products at all stages
- Comprehensive customer support right through to realisation of facilities
- Design and construction of specific system components
- Adaptation and installation into new or existing production facilities
- Technical maintenance of facilities
- Long-term collaboration for development of new or existing products, or exchange of facility components

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